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High-performance MoS₂ transistors with low-resistance molybdenum contacts

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#	Paper	IF	Citations
301	A Compact Current-Voltage Model for 2D Semiconductor Based Field-Effect Transistors Considering Interface Traps, Mobility Degradation, and Inefficient Doping Effect. 2014 , 61, 4282-4290		94
300	Engineering electronic properties of metal/MoSe ₂ interfaces using self-assembled monolayers. 2014 , 2, 9842-9849		21
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297	Performance evaluation and design considerations of 2D semiconductor based FETs for sub-10 nm VLSI. 2014 ,		16
296	Spin-valley relaxation and quantum transport regimes in two-dimensional transition-metal dichalcogenides. 2014 , 90,		33
295	Interface engineering for high-performance top-gated MoS ₂ field-effect transistors. 2014 , 26, 6255-61		227
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